

36. (Amended) A semiconductor device claimed in Claim 35, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

G² 37. (Amended) A semiconductor device claimed in Claim 34, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

G³ 41. (Amended) A semiconductor device claimed in Claim 40, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

42. (Amended) A semiconductor device claimed in Claim 38, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

G⁴ 45. (Amended) A semiconductor device claimed in Claim 44, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

46. (Amended) A semiconductor device claimed in Claim 43, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a

HAYES SOLOWAY P.C.
130 W. CUSHING ST.
TUCSON, AZ 85701
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567